## Abstract Submitted for the MAR05 Meeting of The American Physical Society

Optical Homogeneous Linewidths and Spectral Diffusion at 1.5 microns in Mixed Er<sup>3+</sup>:Eu<sup>3+</sup>:Y<sub>2</sub>SiO<sub>5</sub> Studied by Photon Echo<sup>1</sup> R.L. CONE, T. BÖTTGER<sup>2</sup>, C.W. THIEL, Y. SUN<sup>3</sup>, Montana State University — Er<sup>3+</sup>-doped materials are important for spectral hole burning applications at 1.5 micron communication wavelengths, including analog signal processing and laser frequency stabilization. Doping Er<sup>3+</sup>:Y<sub>2</sub>SiO<sub>5</sub> with Eu<sup>3+</sup> is shown to broaden the inhomogeneous linewidth of the  ${}^4\mathrm{I}_{15/2}$  -  ${}^4\mathrm{I}_{13/2}$  transition without significantly broadening the homogeneous linewidth. This maximizes bandwidth in real-time analog signal processing applications without compromising resolution. Photon echo and stimulated photon echo decays between 1.5 K and 5.5 K were measured along with angle-dependent Zeeman spectra and site-selective absorption and emission. Detailed modeling of observed spectral diffusion induced by spin dynamics considered Er<sup>3+</sup>-Er<sup>3+</sup> dipole interactions driven by direct-phonon processes. The model describes and explains observed behavior and predicts behavior vs. magnetic field, crystal temperature, Er<sup>3+</sup> dopant concentration, and crystal orientation. \* Currently at University of San Francisco \*\* Currently at University of South Dakota

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